

# ISC3247AS1

FOR RELAY DRIVE, POWER SUPPLY APPLICATION  
SILICON NPN EPITAXIAL TYPE

## DESCRIPTION

ISC3247AS1 is a silicon NPN epitaxial type transistor.

Designed with high voltage, high collector current, dissipation and high hFE.

## FEATURE

- High hFE.  $hFE=600$  to  $1800$
- High voltage.  $V_{CE0}=50V$
- Low collector to emitter saturation voltage.  
 $V_{CE(sat)}=0.15V$  ( $I_C=500mA, I_B=10mA$ )
- High collector dissipation.  $P_C=600mW$

## APPLICATION

Relay drive or power supply for audio machine, VCR, and other electronic machine.

## MAXIMUM RATINGS ( $T_a=25^\circ C$ )

Symbol	Parameter	Ratings	Unit
$V_{CBO}$	Collector to Base voltage	50	V
$V_{EBO}$	Emitter to Base voltage	6	V
$V_{CEO}$	Collector to Emitter voltage	50	V
$I_C$	Collector current	1	A
$I_{CM}$	Peak collector current	2	A
$P_c$	Collector dissipation	600	mW
$T_j$	Junction temperature	+150	$^\circ C$
$T_{stg}$	Storage temperature	-55~+150	$^\circ C$

## ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ C$ )

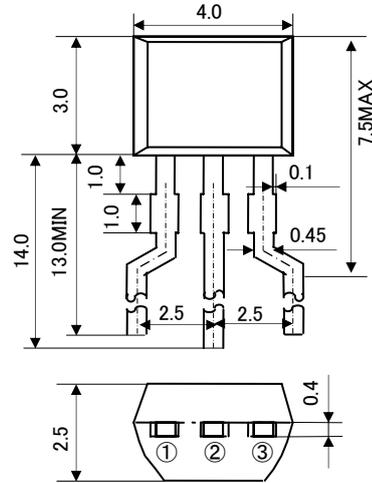
Parameter	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
$V_{(BR)CBO}$	C to B break down voltage	$I_C=10\mu A, I_E=0mA$	50	-	-	V
$V_{(BR)EBO}$	E to B break down voltage	$I_E=10\mu A, I_C=0mA$	6	-	-	V
$V_{(BR)CEO}$	C to E break down voltage	$I_C=1mA, R_{BE}=\infty$	50	-	-	V
ICBO	Collector cut off current	$V_{CB}=40V, I_E=0mA$	-	-	0.1	$\mu A$
IEBO	Emitter cut off current	$V_{EB}=2V, I_C=0mA$	-	-	0.1	$\mu A$
hFE※	DC forward current gain	$V_{CE}=6V, I_C=0.1A$	600	-	1800	-
VCE(sat)	C to E Saturation Voltage	$I_C=500mA, I_B=10mA$	-	0.15	0.5	V
fT	Gain band width product	$V_{CE}=10V, I_E=-10mA$	-	130	-	MHz
Cob	Collector output capacitance	$V_{CB}=10V, I_E=0mA, f=1MHz$	-	12	-	pF

※) It shows hFE classification in right table.

Item	H	J
hFE item	600~1200	900~1800

## OUTLINE DRAWING

Unit:mm



JEITA:  
JEDEC:

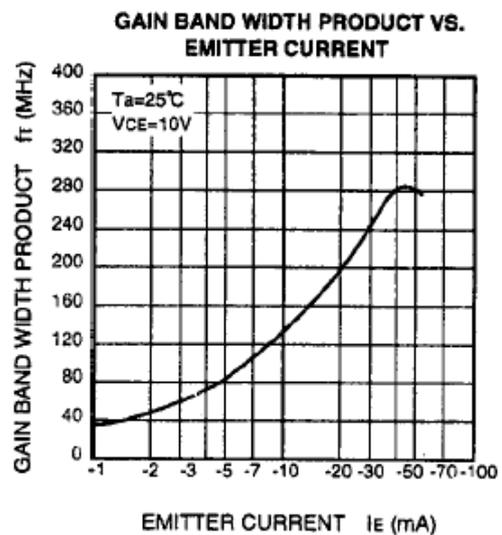
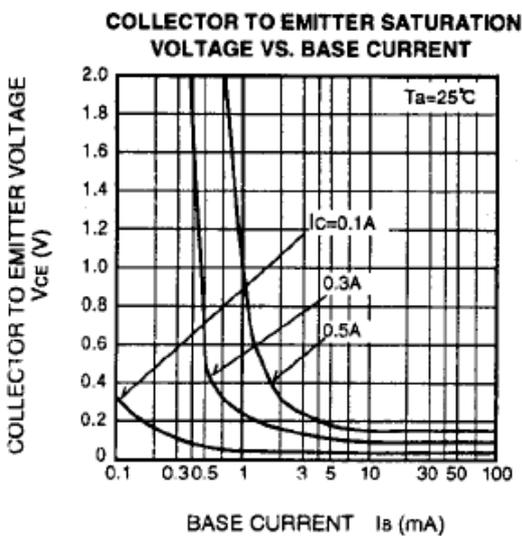
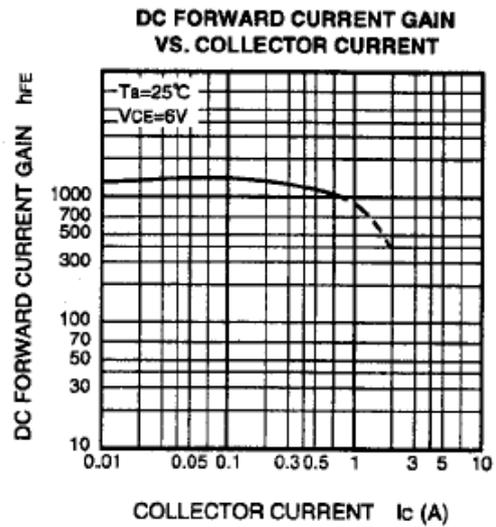
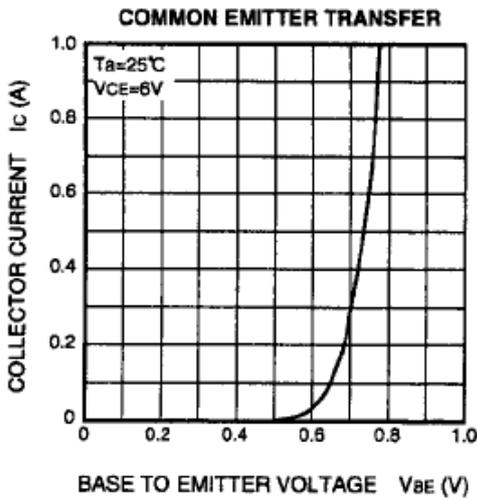
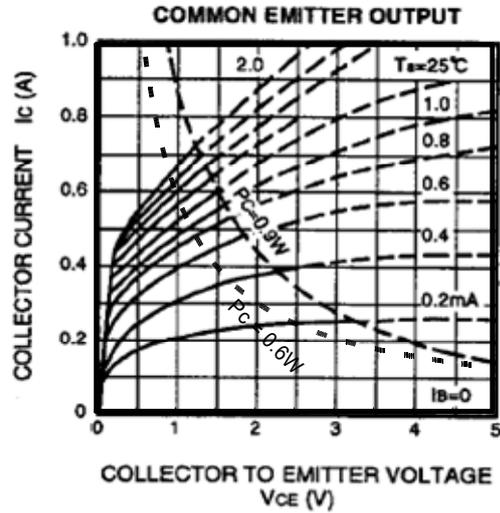
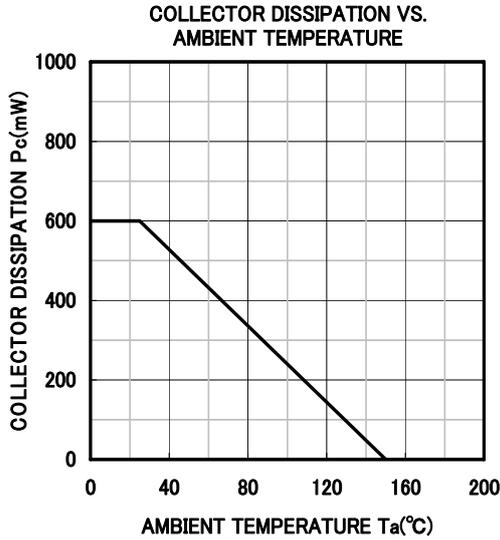
## TERMINAL CONNECTER

- ①: EMITTER
- ②: COLLECTOR
- ③: BASE

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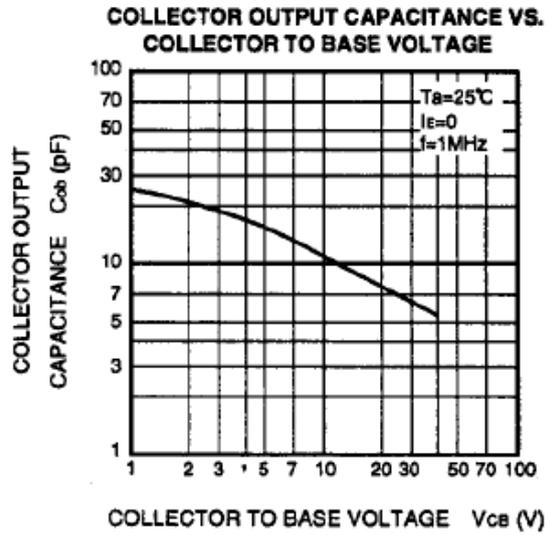
## TYPICAL CHARACTERISTICS



<SMALL-SIGNAL TRANSISTOR>

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